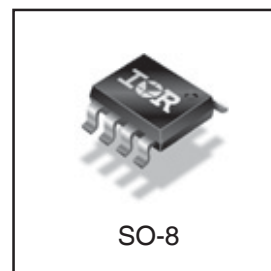
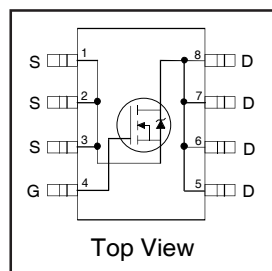


HEXFET® Power MOSFET

| | | |
|---|------------|-----------|
| V_{DS} | 20 | V |
| $R_{DS(on) max}$ (@ $V_{GS} = 10V$) | 4.4 | mΩ |
| Q_g (typical) | 22 | nC |
| I_D (@ $T_A = 25^\circ C$) | 20 | A |



Applications

- Synchronous MOSFET for Notebook Processor Power
- Synchronous Rectifier MOSFET for Isolated DC-DC Converters in Networking Systems

Features

| |
|---|
| Industry-standard pinout SO-8 Package |
| Compatible with Existing Surface Mount Techniques |
| RoHS Compliant, Halogen-Free |
| MSL1, Industrial qualification |



Benefits

| |
|----------------------------|
| Multi-Vendor Compatibility |
| Easier Manufacturing |
| Environmentally Friendlier |
| Increased Reliability |

| Base Part Number | Package Type | Standard Pack | | Orderable Part Number |
|------------------|--------------|---------------|----------|-----------------------|
| | | Form | Quantity | |
| IRF3717PbF-1 | SO-8 | Tube/Bulk | 95 | IRF3717PbF-1 |
| | | Tape and Reel | 4000 | IRF3717TRPbF-1 |

Absolute Maximum Ratings

| | Parameter | Max. | Units |
|--------------------------|--|--------------|-------|
| V_{DS} | Drain-to-Source Voltage | 20 | V |
| V_{GS} | Gate-to-Source Voltage | ± 20 | |
| $I_D @ T_A = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 20 | A |
| $I_D @ T_A = 70^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 16 | |
| I_{DM} | Pulsed Drain Current ① | 160 | |
| $P_D @ T_A = 25^\circ C$ | Power Dissipation | 2.5 | W |
| $P_D @ T_A = 70^\circ C$ | Power Dissipation | 1.6 | |
| | Linear Derating Factor | 0.02 | W/°C |
| T_J | Operating Junction and | -55 to + 150 | °C |
| T_{STG} | Storage Temperature Range | | |

Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|-----------------|------------------------|------|------|-------|
| $R_{\theta JL}$ | Junction-to-Drain Lead | — | 20 | °C/W |
| $R_{\theta JA}$ | Junction-to-Ambient ④ | — | 50 | |

Notes ① through ④ are on page 10

Static @ T_J = 25°C (unless otherwise specified)

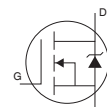
| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---------------------------------------|---|------|-------|------|-------|---|
| BV _{DSS} | Drain-to-Source Breakdown Voltage | 20 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| ΔBV _{DSS} /ΔT _J | Breakdown Voltage Temp. Coefficient | — | 0.014 | — | V/°C | Reference to 25°C, I _D = 1mA |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | 3.7 | 4.4 | mΩ | V _{GS} = 10V, I _D = 20A ③ |
| | | — | 4.8 | 5.7 | | V _{GS} = 4.5V, I _D = 16A ③ |
| V _{GS(th)} | Gate Threshold Voltage | 1.55 | 2.0 | 2.45 | V | V _{DS} = V _{GS} , I _D = 250μA |
| ΔV _{GS(th)} /ΔT _J | Gate Threshold Voltage Coefficient | — | -5.4 | — | mV/°C | |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | 1.0 | μA | V _{DS} = 16V, V _{GS} = 0V |
| | | — | — | 150 | | V _{DS} = 16V, V _{GS} = 0V, T _J = 125°C |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | 100 | nA | V _{GS} = 20V |
| | Gate-to-Source Reverse Leakage | — | — | -100 | | V _{GS} = -20V |
| g _{fs} | Forward Transconductance | 57 | — | — | S | V _{DS} = 10V, I _D = 16A |
| Q _g | Total Gate Charge | — | 22 | 33 | nC | V _{DS} = 10V V _{GS} = 4.5V I _D = 16A See Fig. 16 |
| Q _{gs1} | Pre-V _{th} Gate-to-Source Charge | — | 6.8 | — | | |
| Q _{gs2} | Post-V _{th} Gate-to-Source Charge | — | 2.2 | — | | |
| Q _{gd} | Gate-to-Drain Charge | — | 7.3 | — | | |
| Q _{godr} | Gate Charge Overdrive | — | 5.7 | — | | |
| Q _{sw} | Switch Charge (Q _{gs2} + Q _{gd}) | — | 9.5 | — | nC | V _{DS} = 10V, V _{GS} = 0V |
| Q _{oss} | Output Charge | — | 12 | — | | |
| t _{d(on)} | Turn-On Delay Time | — | 12 | — | ns | V _{DD} = 10V, V _{GS} = 4.5V I _D = 16A Clamped Inductive Load |
| t _r | Rise Time | — | 14 | — | | |
| t _{d(off)} | Turn-Off Delay Time | — | 15 | — | | |
| t _f | Fall Time | — | 6.0 | — | | |
| C _{iss} | Input Capacitance | — | 2890 | — | pF | V _{GS} = 0V V _{DS} = 10V f = 1.0MHz |
| C _{oss} | Output Capacitance | — | 930 | — | | |
| C _{rss} | Reverse Transfer Capacitance | — | 430 | — | | |

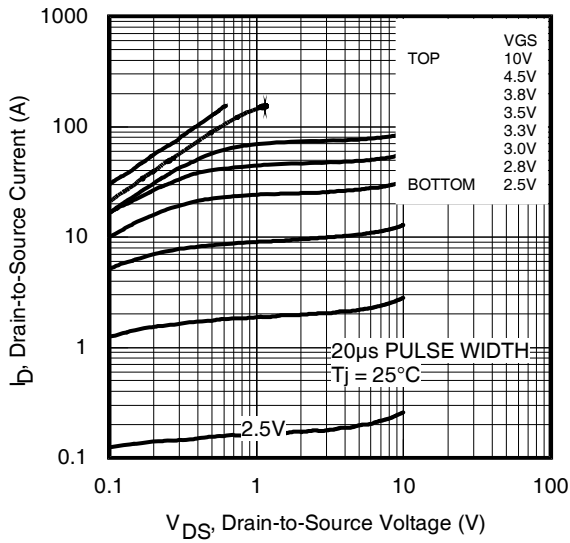
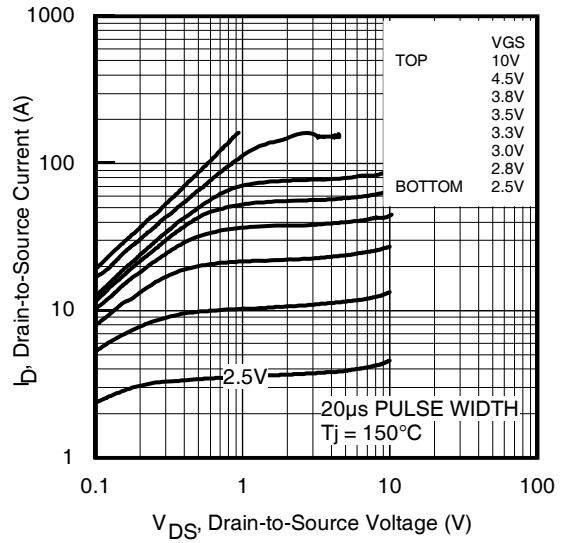
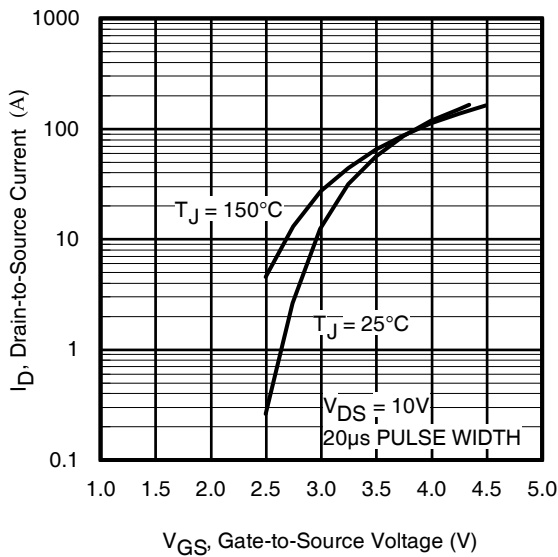
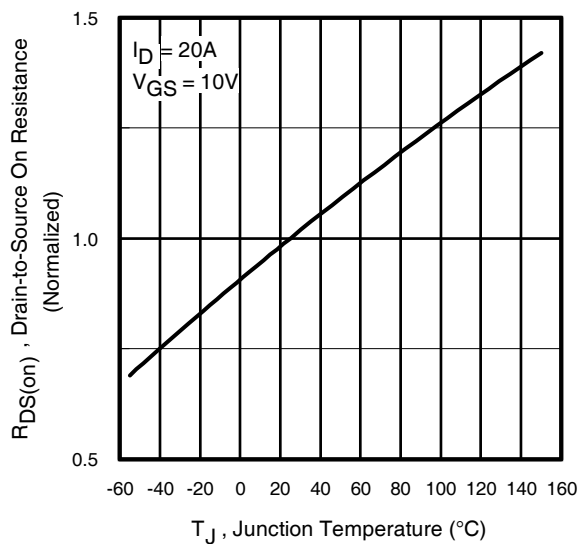
Avalanche Characteristics

| | Parameter | Typ. | Max. | Units |
|-----------------|---------------------------------|------|------|-------|
| E _{AS} | Single Pulse Avalanche Energy ② | — | 32 | mJ |
| I _{AR} | Avalanche Current ① | — | 16 | A |

Diode Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-----------------|---|------|------|------|-------|---|
| I _S | Continuous Source Current (Body Diode) | — | — | 20 | A | MOSFET symbol showing the integral reverse p-n junction diode. |
| I _{SM} | Pulsed Source Current (Body Diode) ① | — | — | 160 | | |
| V _{SD} | Diode Forward Voltage | — | — | 1.0 | V | T _J = 25°C, I _S = 16A, V _{GS} = 0V ③ |
| t _{rr} | Reverse Recovery Time | — | 22 | 32 | ns | T _J = 25°C, I _F = 16A, V _{DD} = 10V |
| Q _{rr} | Reverse Recovery Charge | — | 13 | 19 | nC | di/dt = 100A/μs ③ |




Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance vs. Temperature

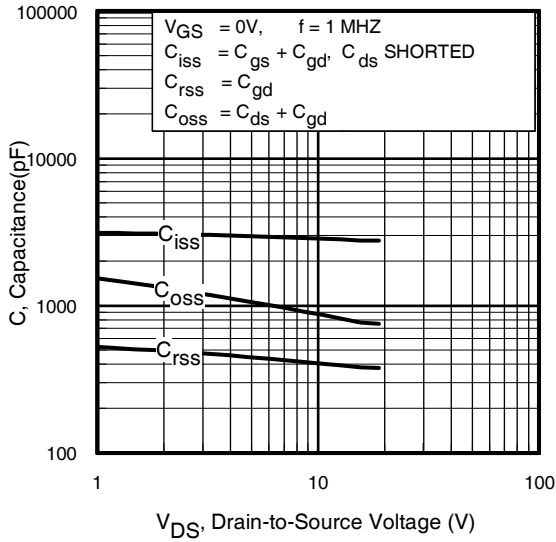


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

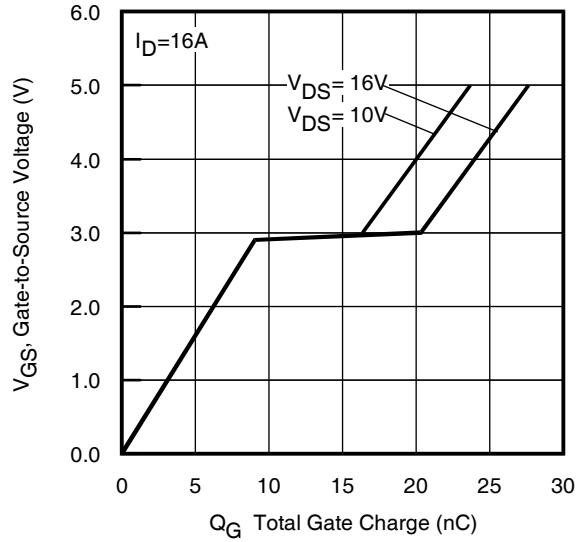


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

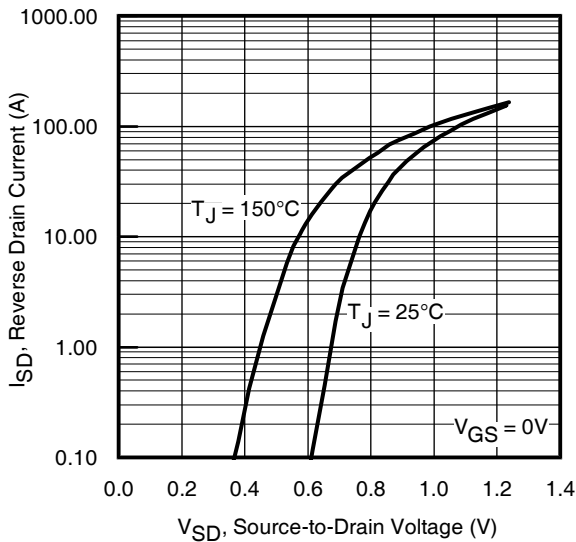


Fig 7. Typical Source-Drain Diode Forward Voltage

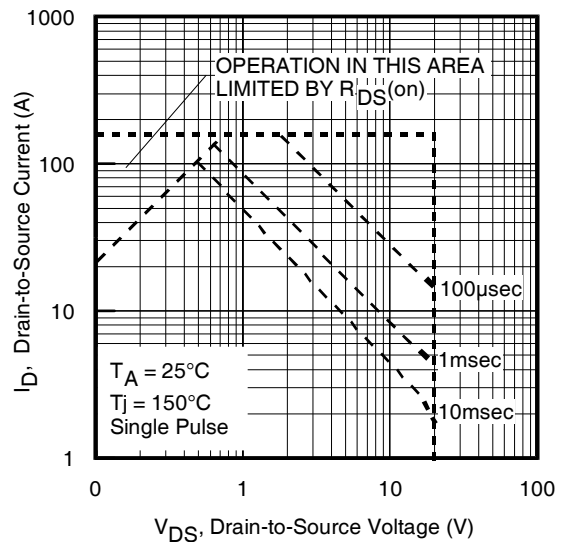
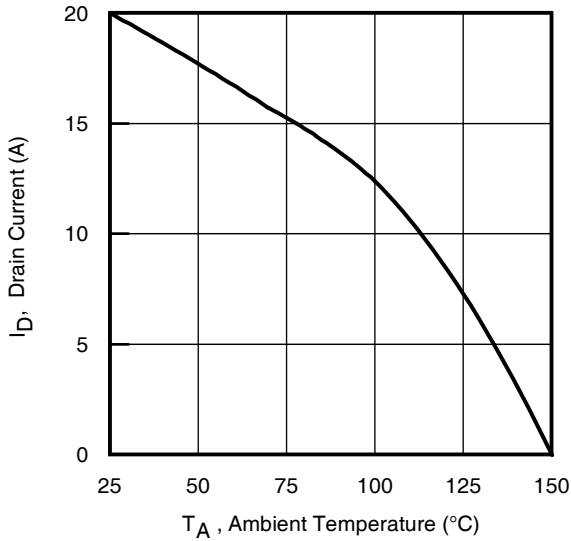
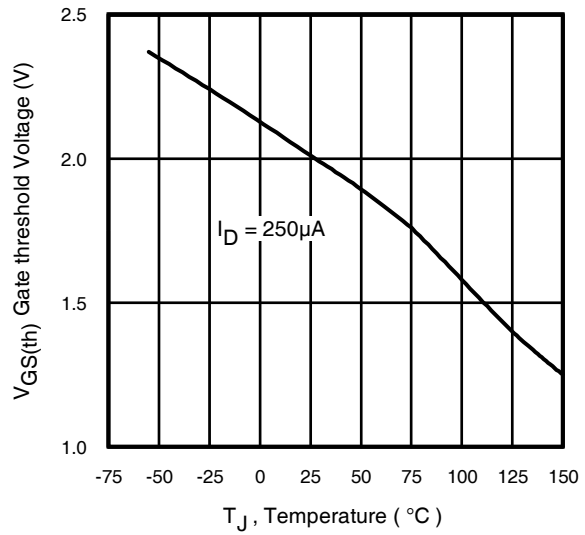
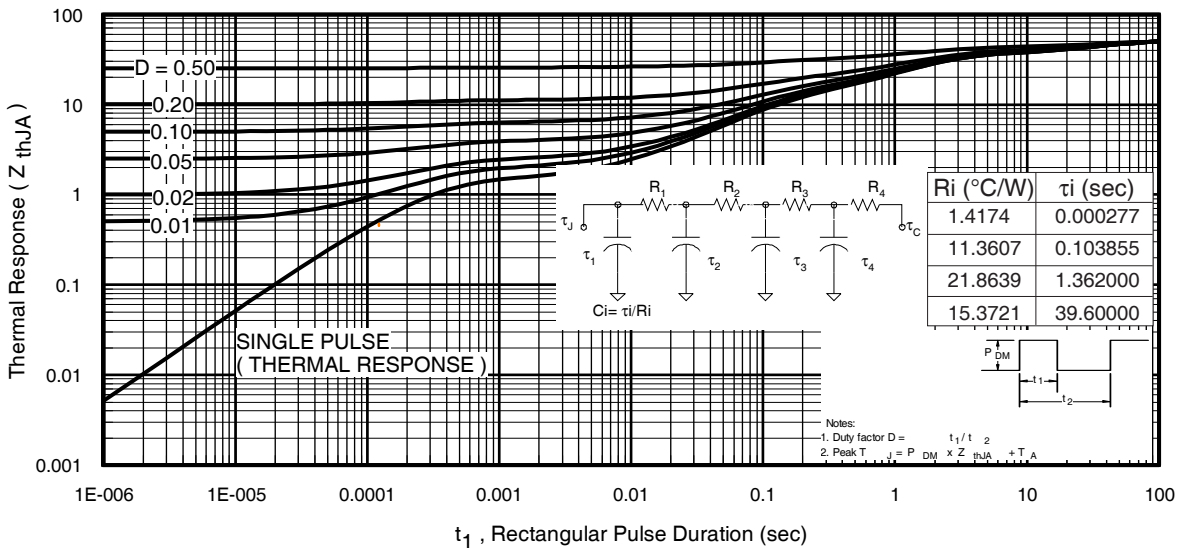
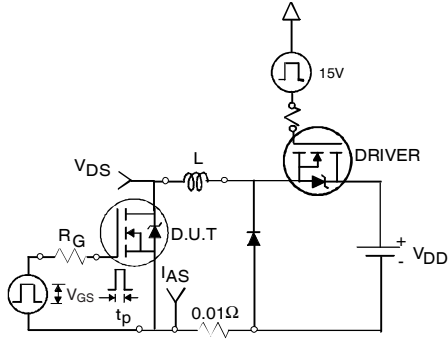
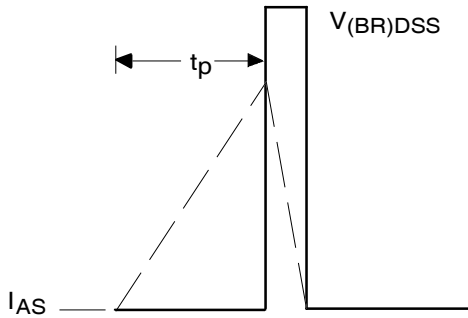
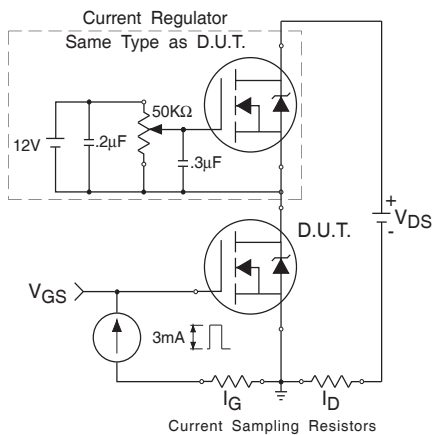
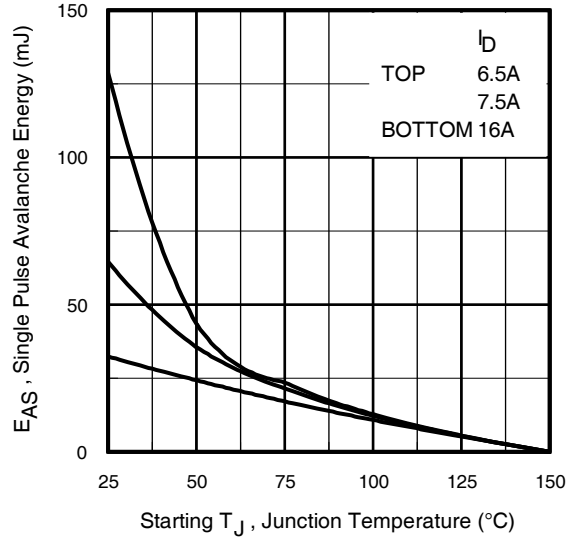
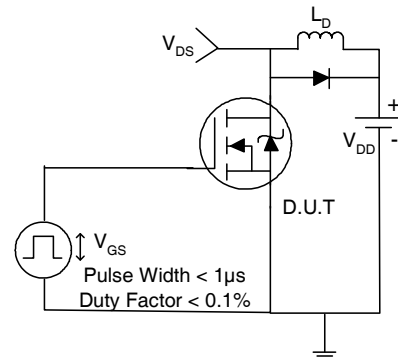
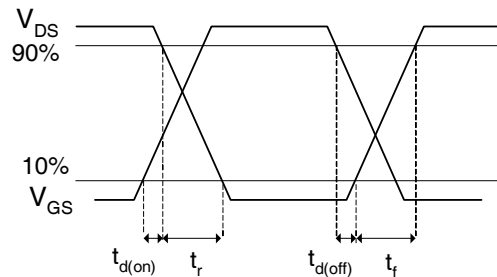


Fig 8. Maximum Safe Operating Area


Fig 9. Maximum Drain Current vs. Ambient Temperature

Fig 10. Threshold Voltage vs. Temperature

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient


Fig 12a. Unclamped Inductive Test Circuit

Fig 12b. Unclamped Inductive Waveforms

Fig 13. Gate Charge Test Circuit

Fig 12c. Maximum Avalanche Energy vs. Drain Current

Fig 14a. Switching Time Test Circuit

Fig 14b. Switching Time Waveforms

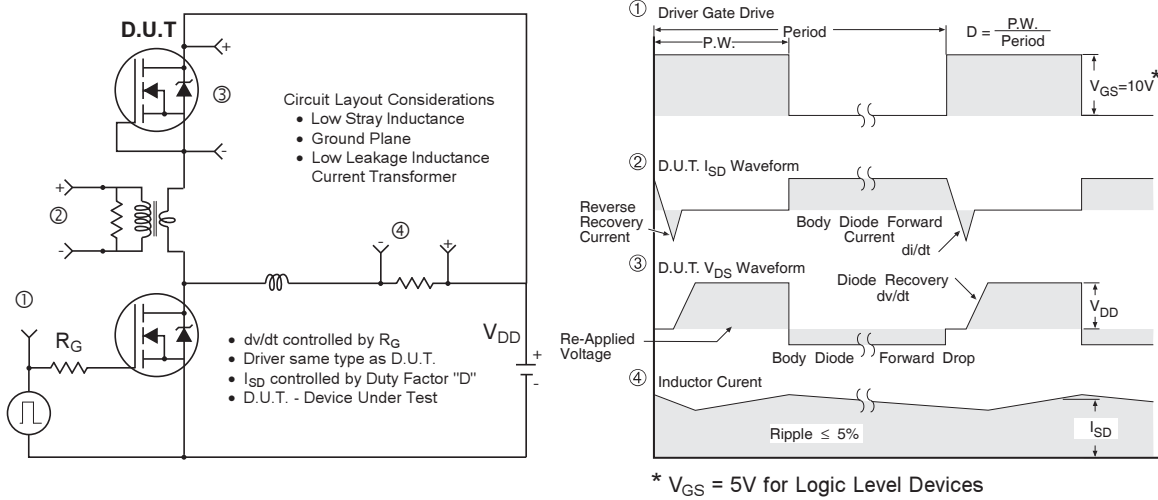


Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

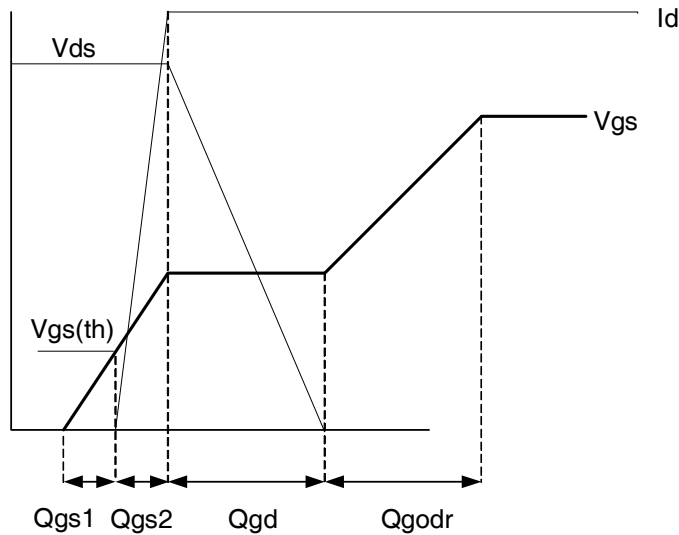


Fig 16. Gate Charge Waveform

Power MOSFET Selection for Non-Isolated DC/DC Converters

Control FET

Special attention has been given to the power losses in the switching elements of the circuit - Q1 and Q2. Power losses in the high side switch Q1, also called the Control FET, are impacted by the $R_{ds(on)}$ of the MOSFET, but these conduction losses are only about one half of the total losses.

Power losses in the control switch Q1 are given by;

$$P_{loss} = P_{conduction} + P_{switching} + P_{drive} + P_{output}$$

This can be expanded and approximated by;

$$P_{loss} = (I_{rms}^2 \times R_{ds(on)}) + \left(I \times \frac{Q_{gd}}{i_g} \times V_{in} \times f \right) + \left(I \times \frac{Q_{gs2}}{i_g} \times V_{in} \times f \right) + (Q_g \times V_g \times f) + \left(\frac{Q_{oss}}{2} \times V_{in} \times f \right)$$

This simplified loss equation includes the terms Q_{gs2} and Q_{oss} which are new to Power MOSFET data sheets.

Q_{gs2} is a sub element of traditional gate-source charge that is included in all MOSFET data sheets. The importance of splitting this gate-source charge into two sub elements, Q_{gs1} and Q_{gs2} , can be seen from Fig 16.

Q_{gs2} indicates the charge that must be supplied by the gate driver between the time that the threshold voltage has been reached and the time the drain current rises to I_{dmax} at which time the drain voltage begins to change. Minimizing Q_{gs2} is a critical factor in reducing switching losses in Q1.

Q_{oss} is the charge that must be supplied to the output capacitance of the MOSFET during every switching cycle. Figure A shows how Q_{oss} is formed by the parallel combination of the voltage dependant (non-linear) capacitance's C_{ds} and C_{dg} when multiplied by the power supply input buss voltage.

Synchronous FET

The power loss equation for Q2 is approximated by;

$$P_{loss} = P_{conduction} + P_{drive} + P_{output}^*$$

$$P_{loss} = (I_{rms}^2 \times R_{ds(on)}) + (Q_g \times V_g \times f) + \left(\frac{Q_{oss}}{2} \times V_{in} \times f \right) + (Q_{rr} \times V_{in} \times f)$$

*dissipated primarily in Q1.

For the synchronous MOSFET Q2, $R_{ds(on)}$ is an important characteristic; however, once again the importance of gate charge must not be overlooked since it impacts three critical areas. Under light load the MOSFET must still be turned on and off by the control IC so the gate drive losses become much more significant. Secondly, the output charge Q_{oss} and reverse recovery charge Q_{rr} both generate losses that are transferred to Q1 and increase the dissipation in that device. Thirdly, gate charge will impact the MOSFETs' susceptibility to Cdv/dt turn on.

The drain of Q2 is connected to the switching node of the converter and therefore sees transitions between ground and V_{in} . As Q1 turns on and off there is a rate of change of drain voltage dV/dt which is capacitively coupled to the gate of Q2 and can induce a voltage spike on the gate that is sufficient to turn the MOSFET on, resulting in shoot-through current. The ratio of Q_{gd}/Q_{gs1} must be minimized to reduce the potential for Cdv/dt turn on.

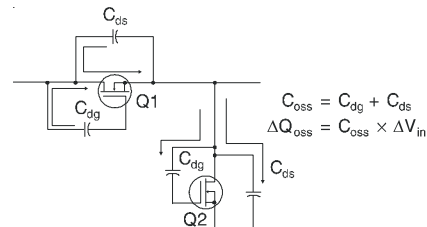
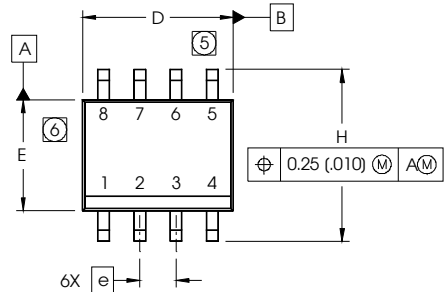


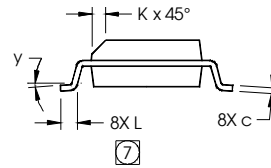
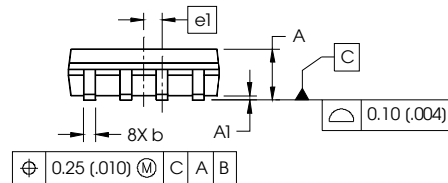
Figure A: Q_{oss} Characteristic

SO-8 Package Outline

Dimensions are shown in millimeters (inches)



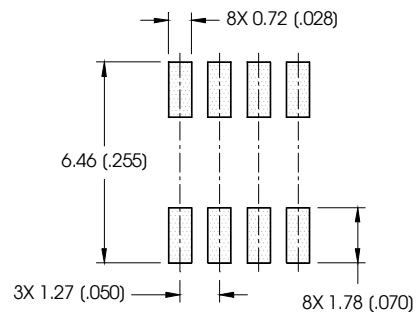
| DIM | INCHES | | MILLIMETERS | |
|-----|------------|-------|-------------|------|
| | MIN | MAX | MIN | MAX |
| A | .0532 | .0688 | 1.35 | 1.75 |
| A1 | .0040 | .0098 | 0.10 | 0.25 |
| b | .013 | .020 | 0.33 | 0.51 |
| c | .0075 | .0098 | 0.19 | 0.25 |
| D | .189 | .1968 | 4.80 | 5.00 |
| E | .1497 | .1574 | 3.80 | 4.00 |
| e | .050 BASIC | | 1.27 BASIC | |
| e1 | .025 BASIC | | 0.635 BASIC | |
| H | .2284 | .2440 | 5.80 | 6.20 |
| K | .0099 | .0196 | 0.25 | 0.50 |
| L | .016 | .050 | 0.40 | 1.27 |
| y | 0° | 8° | 0° | 8° |



NOTES:

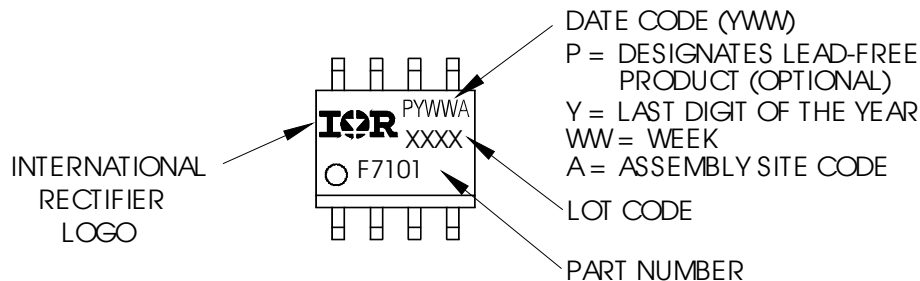
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO SUBSTRATE.

FOOTPRINT

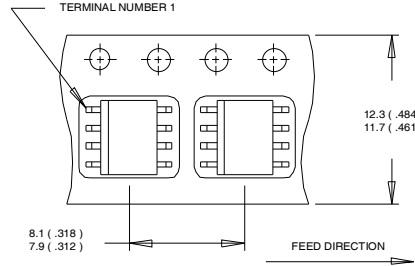


SO-8 Part Marking

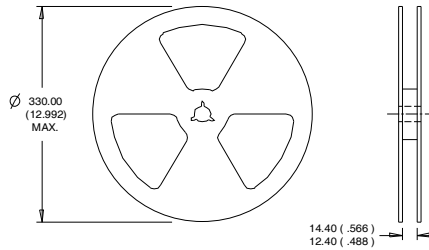
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

SO-8 Tape and Reel Dimensions are shown in millimeters (inches)


- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification information[†]

| | | |
|----------------------------|--|---|
| Qualification level | Industrial (per JEDEC JESD47F ^{††} guidelines) | |
| Moisture Sensitivity Level | SO-8 | MSL1 (per JEDEC J-STD-020D ^{††}) |
| RoHS compliant | Yes | |

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

^{††} Applicable version of JEDEC standard at the time of product release

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.26\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 16\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board.

International
 Rectifier

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA

To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>

单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon Technologies\(英飞凌\)](#)